

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Marshall et al.

Docket No.: TI-31157

Serial No: TBD

Examiner: TBD

Filed: 12/13/01

Art Unit: TBD

For: MEMORY CELL WITH TRANSISTORS HAVING RELATIVELY HIGH  
THRESHOLD VOLTAGES IN RESPONSE TO SELECTIVE GATE  
DOPING

PRELIMINARY AMENDMENT

December 13, 2001

Assistant Commissioner for Patents

Washington, DC 20231

Dear Sir:

Please amend the above referenced application as follows:

In the Specification:

Page 1, before line 1, insert --This application claims priority under 35 USC §  
119(e)(1) of provisional application number **60/259,324** filed **01/03/01**.